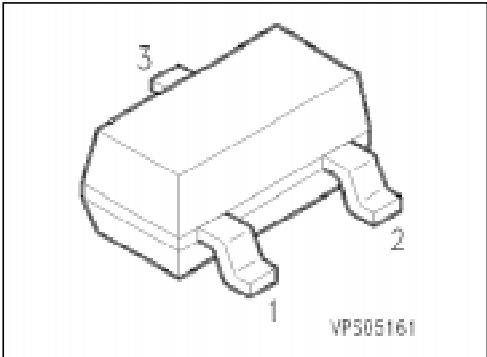
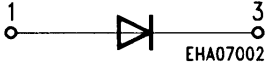
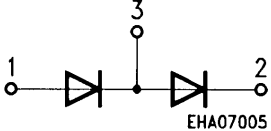
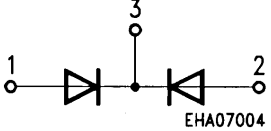
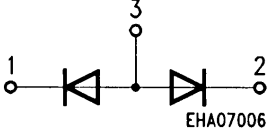


Silicon RF Switching Diode

BAT 18 ...

- Low-loss VHF/UHF switch above 10 MHz
- Pin diode with low forward resistance



Type	Marking	Ordering Code	Pin Configuration	Package ¹⁾
BAT 18	A2	Q62702-A787		SOT 23
BAT 18-04	AU	Q62702-A938		
BAT 18-05	AS	Q62702-A940		
BAT 18-06	AT	Q62702-A942		

Maximum Ratings per Diode

Parameter	Symbol	Values	Unit
Reverse voltage	V_R	35	V
Forward current	I_F	100	mA
Operating and storage temperature range	T_{op} T_{stg}	- 55 ... + 150	°C

Thermal Resistance

Junction - ambient	$R_{th JA}$	≤ 450	K/W
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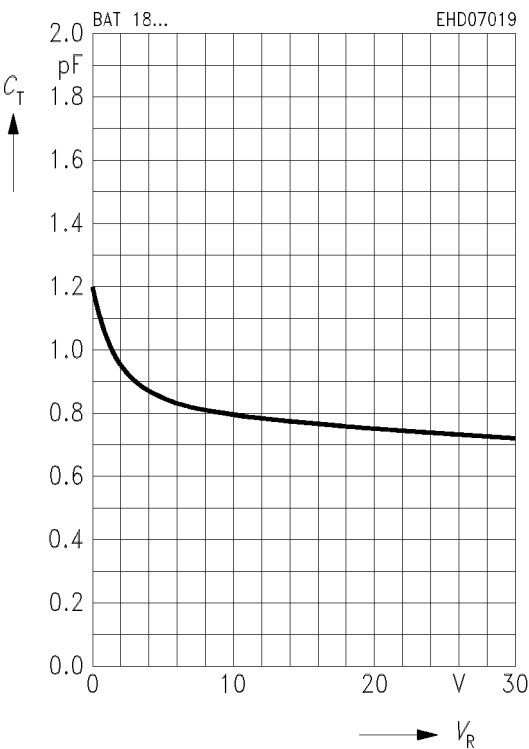
¹⁾ For detailed information see chapter Package Outlines.
²⁾ Package mounted on alumina 15 mm × 16.7 mm × 0.7 mm.

Electrical Characteristics per Diode

at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Forward voltage $I_F = 100\text{ mA}$	V_F	—	0.38	1.2	V
Reverse current $V_R = 20\text{ V}$ $V_R = 20\text{ V}, T_A = 60\text{ }^{\circ}\text{C}$	I_R	— —	— —	20 200	nA
Diode capacitance $V_R = 20\text{ V}, f = 1\text{ MHz}$	C_T	—	0.75	1	pF
Forward resistance $I_F = 5\text{ mA}, f = 100\text{ MHz}$	r_f	—	0.4	0.7	Ω
Series inductance	L_S	—	2	—	nH

Diode capacitance $C_T = f(V_R)$ $f = 1\text{ MHz}$



Forward resistance $r_f = f(I_F)$ $f = 100\text{ MHz}$

